

## TITLE OF THE INVENTION

DEPOSITION MASK FRAME ASSEMBLY, METHOD OF FABRICATING THE SAME, AND  
METHOD OF FABRICATING ORGANIC ELECTROLUMINESCENT DEVICE USING THE  
DEPOSITION MASK FRAME ASSEMBLY

## CROSS-REFERENCE TO RELATED APPLICATIONS

**[0001]** This application claims the benefit of Japanese Application No. 2002-339616, filed November 22, 2002, in the Japanese Intellectual Property Office, the disclosure of which is incorporated herein by reference.

## BACKGROUND OF THE INVENTION

### 1. Field of the Invention

**[0002]** The present invention relates to a deposition mask frame assembly, a method of fabricating the same, and a method of fabricating an organic electroluminescent (EL) device using the deposition mask frame assembly, and more, particularly, to a mask frame assembly for depositing a thin film that constitutes an organic EL device.

### 2. Description of the Related Art

**[0003]** EL devices, which are spontaneous light-emitting display devices, provide a wide viewing angle, a good contrast, and a high response speed. Accordingly, much attention has been recently paid to EL devices because they can be used as next-generation display devices.

**[0004]** EL devices are classified into inorganic EL devices or organic EL devices, depending on what material is used to form a light-emitting layer. Organic EL devices have a higher brightness and faster responsivity than inorganic EL devices, and can provide color display, so they are being actively developed of late.

**[0005]** Such organic EL devices include first electrodes formed in a predetermined pattern on a transparent insulating substrate, an organic film formed on the first electrodes by vacuum

deposition, and second electrodes formed as a cathode electrode layer on the organic film such that the first and second electrodes cross each other.

**[0006]** In the manufacture of the organic EL devices having such a structure, the first electrodes are typically formed by patterning indium tin oxide (ITO) using a photolithographic method.

**[0007]** Such a photolithographic method can be used before an organic film is formed, but causes a problem when it is used after an organic film is formed. Because the organic film is very susceptible to damage from water, it must be thoroughly isolated from water while being fabricated, and even after the fabrication. Moreover, the photolithographic method includes an exposure to water during the peeling-off and etching of the resist, so it is not suitable for the organic film and the cathode electrode layer.

**[0008]** This problem is usually solved by vacuum-depositing an organic light emissive material for the organic film, and a material for the cathode electrode layer, using a patterned mask. In particular, the cathode electrode layer can be patterned using a cathode separator, which is a predetermined separation wall, but it is known that a vacuum deposition is the most appropriate method to pattern an organic film formed of a low molecular organic material.

**[0009]** A technique of patterning an organic film, which is a light-emitting layer, using a mask is very important in the manufacture of full-color organic EL devices.

**[0010]** Examples of conventional full-color organic EL device coloring methods include a three-color independent deposition method of independently depositing red (R), green (G), and blue (B) color pixels on a substrate, a color conversion method (CCM) of forming a color conversion layer on a light emissive surface using a blue light source, and a color filtering method which uses a white light source and a color filter. The three-color independent deposition method is very popular because of the simplicity of the procedure, and because it provides a high color purity and efficiency.

**[0011]** In the three-color independent deposition method, a highly accurate mask must be used to independently deposit R, G, and B color pixels on a substrate. In particular, a high accuracy of the positions of the deposited pixels, that is, a high accuracy of the widths of pattern apertures, is required, and a high accuracy of a total mask pitch is also required.

**[0012]** A mask 10 used to deposit an organic film or electrodes during the fabrication of an organic EL device is typically supported by a frame 20, so that the mask 10 is tensed as shown in FIG. 1. The mask 10 is comprised of a single metal thin plate 11 and masking pattern units 12, which allow a plurality of substrate units that constitute an organic EL device to be deposited on the metal thin plate 11.

**[0013]** Because the mask 10 is thinly formed and minutely patterned, some parts of it may droop if it is used without any treatment, preventing an accurate patterning. Accordingly, as shown in FIG. 1, an optimal tension is applied to the mask 10 to obtain a predetermined accuracy of a total pitch (Pt), and the tensed mask 10 is coupled to the mask frame 20. Upon the coupling, it is important to not change the Pt accuracy. The coupling of the mask 10 to the mask frame 20 can be achieved by various methods such as using an adhesive, by laser welding, or by resistance welding.

**[0014]** The mask 10 may be fabricated by etching or electro-forming.

**[0015]** In the manufacture of the mask 10 by etching, a photoresist layer having a pattern of slits is formed on a thin plate, or a film having a pattern of slits is attached to a thin plate, and then the resulting plate is etched.

**[0016]** However, as masks are enlarged and the pattern of the slits becomes fine, the mask forming method based on etching cannot equalize the tolerance of the width of the mask to the tolerance of the edges of the slits. In particular, when the mask 10 is manufactured by etching a thin plate, the thin plate may be over-etched or under-etched. In this case, the sizes of the slits may not be standardized.

**[0017]** On the other hand, the electro-forming method has a principle that a metal is deposited on a prototype to a desired thickness by the electrolysis of a metallic salt solution through an operation such as electrical plating, and then peeled off from the prototype to obtain a metal product having an uneven surface whose prominences and depressions are arranged opposite to those of the prototype. According to this principle, a mask is fabricated.

**[0018]** In the method of fabricating a mask by the electro-forming method, an alloy of nickel (Ni) and cobalt (Co) is used as the material of the mask. The use of the Ni-Co alloy increases the roughness of a fabricated surface and the accuracy of a slot pattern. On the other hand,

because the Ni-Co alloy has a poor weldability, a crack may be generated in the mask when the Ni-Co alloy is welded into a frame. In other words, when cobalt is alloyed with another metal, its hardness and intensity increase, and accordingly its fragility increases, which helps a crack to be easily generated upon welding.

**[0019]** This crack generation can be seen from FIGS. 2A through 2C. Referring to FIG. 2A, when the mask 10 and the frame 20 are welded by a laser welder 21, a gap 14 is generated around a joint 13 by heat flexion. If the welding continues on the resultant structure having the gap 14 as shown in FIG. 2B, a crack 15 is generated as shown in FIG. 2C. Due to this crack generation, the tension which supports a mask partially decreases, and accordingly the accuracy of the total pitch of the mask varies. Thus, accurate patterning is impossible.

**[0020]** A mask that overcomes the problem of creeping of strips that form slits due to a thermal expansion of the mask is disclosed in Japanese Patent Publication No. 2001-247961.

**[0021]** The disclosed mask includes a mask portion and a screen portion. The mask portion is a deposition mask used to form a patterning film on a substrate by deposition, and has partitions for defining a plurality of first apertures. The screen portion has a plurality of second apertures smaller than the first apertures, and a magnetic material in which the second apertures are disposed on the first apertures of the mask portion.

**[0022]** Japanese Patent Publication No. 2001-273979 discloses the structure of a magnetic mask. Japanese Patent Publication No. 2001-254169 discloses a deposition mask frame assembly, in which a patterned mask masks a deposition area in a close adherence to a material to be deposited and has finer gaps and finer patterns incapable of supporting a predetermined size than the thickness of a frame. The fine patterns of the patterned mask are supported by fine ribs.

**[0023]** These disclosed masks are closely adhered to a material to be deposited because they are formed of a magnetic material. However, due to the limits of the mask materials, these masks still have fundamental problems, such as a poor welding quality, and a variation in the accuracy of a total pitch due to the poor welding.

**[0024]** Japanese Patent Publication No. 2002-9098 discloses a pattern forming apparatus for preventing a film pre-formed on a substrate from being damaged due to a partial coming-off of a

mask from a frame due to a thermal expansion during deposition. The pattern forming apparatus includes a support which is formed to be larger than the mask and has a dent portion to seat the mask onto the dent portion. The user of the support prevents a mask from being bent in waves due to a thermal expansion during the formation of a film. Also, by forming a magnetic element on the side of the mask other than the side on which the support is formed, the magnetic element makes the mask closer to the substrate so that a space between the mask and the support is created. Thus, the space contributes to cooling the mask.

**[0025]** However, because the disclosed mask having slits is not firmly supported by the frame, the location of the mask cannot be accurately controlled, and the location of the mask may be changed during deposition.

**[0026]** Japanese Patent Publication No. 2002-8859 discloses a pattern forming apparatus for preventing a mask from being expanded by heat during the formation of a film, in which a liquid path is formed within a frame which supports the mask, and a cooling solution circulates within the liquid path. However, this disclosure also has a problem such as a change in the accuracy of a total pitch due to a poor welding of a mask and a frame.

**[0027]** Japanese Patent Publication Nos. 2000-48954, 2000-173769, 2001-203079, and 2001-110567 disclose a metal mask including supplementary lines to prevent drooping of a mask shield between the mask and a frame. These masks also have fundamental problems such as a poor welding quality due to the limits of the material of a mask.

## SUMMARY OF THE INVENTION

**[0028]** The present invention provides a deposition mask frame assembly, a method of fabricating the same, and a method of fabricating an organic electroluminescent (EL) device using the deposition mask frame assembly.

**[0029]** Additional aspects and/or advantages of the invention will be set forth in part in the description which follows and, in part, will be obvious from the description, or may be learned by practice of the invention.

**[0030]** According to an aspect of the present invention, there is provided a deposition mask frame assembly comprising a mask comprising a thin plate in which a predetermined pattern of

apertures is formed, a frame supporting one surface of the mask so that the mask is tensed, and a cover mask supporting an opposite surface of the mask, wherein the cover mask corresponds to the frame.

**[0031]** The mask may be formed of either nickel or an alloy of nickel and cobalt by electro-forming.

**[0032]** The mask, the frame, and the cover mask may be joined together by dot welding. The dot welding may be performed so that a welding pitch, which is an interval between welding dots, is 3mm or less.

**[0033]** According to another aspect of the present invention, there is provided a method of manufacturing a deposition mask frame assembly. This method may include manufacturing a mask by electro-forming, and installing a frame on one surface of the mask and installing a cover mask on the other surface of the mask while the mask is being tensed, and welding the cover mask, the mask, and the frame.

**[0034]** Here, the mask may be electrodeposited of nickel or an alloy of nickel and cobalt.

**[0035]** According to still another aspect of the present invention, there is provided a method of manufacturing an organic EL device. In this method, a first electrode layer is formed in a predetermined pattern on an insulating substrate. Next, an organic film including at least a patterned emission layer is formed on the first electrode layer. Thereafter, a second electrode layer is formed in a predetermined pattern on the organic film. Then, the second electrode layer is sealed. Here, at least one of the organic film and the second electrode layer is deposited using a deposition mask frame assembly. The deposition mask assembly includes a mask including a thin plate in which a predetermined pattern of apertures is formed, a frame supporting one surface of the mask so that the mask is tensed, and a cover mask supporting an opposite surface of the mask, wherein the cover mask corresponds to the frame.

**[0036]** The mask may be formed of nickel or an alloy of nickel and cobalt by electro-forming.

**[0037]** The mask, the frame, and the cover mask may be joined together by dot welding. The dot welding may be performed such that a welding pitch, which is an interval between welding dots, is 3mm or less.

## BRIEF DESCRIPTION OF THE DRAWINGS

**[0038]** These and/or other aspects and advantages of the invention will become apparent and more readily appreciated from the following description of the embodiments, taken in conjunction with the accompanying drawings of which:

FIG. 1 is an exploded perspective view of a conventional mask frame assembly;

FIGS. 2A through 2C are cross-sectional views illustrating a process in which a crack is generated around a joint where a mask made of an alloy of nickel and cobalt joins to a frame;

FIG. 3 is a perspective view of a mask frame assembly according to an embodiment of the present invention;

FIG. 4 is a partial perspective view of the mask of FIG. 3;

FIG. 5 is a cross-sectional view taken along line A-A of FIG. 4;

FIGS. 6A through 6C are perspective views illustrating a process of manufacturing a mask frame assembly according to an embodiment of the present invention;

FIGS. 7A through 7D show a deviation of the total pitch of a mask frame assembly and a line deviation of the mask frame assembly;

FIG. 8 is a graph of a total pitch after a tension is removed after welding versus a welding pitch; and

FIG. 9 is a graph of an aperture efficiency based on a deviation of the widths of apertures of a mask versus a pixel pitch.

## DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

**[0039]** Reference will now be made in detail to the embodiments of the present invention, examples of which are illustrated in the accompanying drawings, wherein like reference numerals refer to the like elements throughout. The embodiments are described below to explain the present invention by referring to the figures.

**[0040]** A mask frame assembly 100 according to an embodiment of the present invention will now be described with reference to FIGS. 3 through 5. Referring to FIG. 3, the mask frame assembly 100 includes a mask 110 having a plurality of mask units 111 and a frame 120 which supports the mask 110 so as to apply a tension to the mask 110. The frame 120 is hollow so as to support the edge of the mask 110 excluding the mask units 111.

**[0041]** As shown in FIG. 4, the mask units 111 include a pattern of apertures 112 which are defined by shielding portions 113. As shown in FIG. 4, the apertures 112 may be formed in an elongated pattern, but they may also be formed in other patterns.

**[0042]** As shown in FIG. 3, the edge of one surface of the mask 110 is supported by the frame 120, while the edge of the opposite surface of the mask 110 is supported by a cover mask 130. The cover mask 130 is configured so as to support the four edges of the mask 120 in FIG. 3, but any configuration that can support the portion of the mask 110 supported by the frame 120 may be used.

**[0043]** The mask 110 may be made of either nickel or an alloy of nickel and cobalt. Preferably, the mask 110 may be made of the nickel-cobalt alloy, which facilitates the formation of fine patterns and provides an excellent surface roughness. The apertures 112 of the mask 110 are formed in a predetermined pattern by an electro-forming method so as to obtain a fine pattern and an excellent surface smoothness. The alloy of Ni and Co may be composed of 85% by weight nickel and 15% by weight cobalt. However, various composition ratios of Ni to Co may be applied.

**[0044]** The cover mask 130 may be formed of Invar, which is mainly composed of Fe and Ni, or 42 alloy, or stainless steel SUS304. Here, SUS denotes special use stainless steel of Japanese Industrial Standards. The frame 120 may be formed of stainless steel SUS410. Moreover, the cover mask 130 or the frame 120 may be formed of various materials.

**[0045]** As shown in FIG. 3, the mask 110, the cover mask 130, and the frame 120 are joined together in such a way that the mask 110 is located between the cover mask 130 and the frame 120. The joining may be achieved using an adhesive agent, preferably by welding. Various welding methods are available such as laser welding or resistance welding. When considering a change in accuracy after the joining, laser welding is preferable. Welding dots 140 of FIG. 3 denote dots used in dot welding using a laser. A welding pitch  $P_w$  is controlled depending on a change in the accuracy of a total pitch after the joining. Preferably, the welding pitch  $P_w$  is controlled to 3mm or less, which will be described later in detail.

**[0046]** As described above, the deposition mask assembly 100 uses the mask 110 manufactured by electro-forming using nickel or a Ni-Co alloy, thus providing an accurate pattern and an excellent surface smoothness. In addition, the deposition mask assembly 100



prevents a crack due to heat refraction at the welding dots by employing the cover mask 130 attached to one side of the mask 110, thus preventing the total pitch from varying due to a poor welding, which is a weak point of the Ni-Co alloy.

**[0047]** FIG. 5 is a cross-sectional view taken along line A-A of FIG. 4. In practice, a surface 113a of the individual shielding portions 113, which contacts a substrate on which a deposition is made, can have a surface smoothness of  $0.1\ \mu\text{m}$ . Each of the apertures 112 can have a width tolerance  $\Delta W_{s1}$  of  $\pm 5\ \mu\text{m}$ . The accuracy of the total pitch  $P_t$  can be  $\pm 10\ \mu\text{m}$ .

**[0048]** A method of manufacturing a deposition mask frame assembly according to an embodiment of the present invention will now be described with reference to FIGS. 6A through 6C.

**[0049]** First, the mask 110 is manufactured by electro-forming. Although not shown in the drawings, a metal layer is electrodeposited on an exposed portion of an electrodepositing plate using an electro-forming method. Here, the electrodepositing plate has a film attached on its area corresponding to shielding portions that form the outer portion of the mask 110 and define the apertures 112. Preferably, the metal layer is formed of nickel or an alloy of nickel and cobalt. Although the metal layer can be electrodeposited to a thickness of about 30 to  $50\ \mu\text{m}$ , the thickness may vary according to the conditions of the user of the mask 110.

**[0050]** After the completion of the electrodeposition for manufacturing the mask 110, the mask 110 is separated from the electrodepositing plate. As shown in FIG. 6A, the mask 110 interposes between the frame 120 and the cover mask 130. Preferably, the inner circumference of the cover mask 130 is made larger than the outer circumference of a substrate (not shown) on which a film is to be deposited, in order to prevent a shadow effect which occurs during deposition when the cover mask 130 contacts the substrate due to a smaller inner circumference of the cover mask 130 than the outer circumference of the substrate.

**[0051]** As shown in FIG. 6B, the mask 110 is clamped and subjected to a tension in directions x and y. Here, the same tension can be applied in directions x and y. However, it is preferable that the four sides are subjected to optimal tensions  $+P_{x1}$  to  $+P_{x5}$ ,  $-P_{x1}$  to  $-P_{x5}$ ,  $+P_{y1}$  to  $+P_{y6}$ , and  $-P_{y1}$  to  $-P_{y6}$ , respectively. In this case, as shown in FIG. 7A, there is no deviation because the total pitches  $P_t$  between two outermost lines 114 and 115 are uniform. As shown in FIGS. 7B and 7C, the total pitch  $P_t$  may have a deviation ( $P_{t\text{ma}} - P_{t\text{min}}$ ). As shown in

FIGS. 7B through 7D, a line deviation ( $\Delta X$ ) may occur. Consequently, the application of different tensions for different sides of the mask can reduce the deviation of the total pitch and the line deviation.

**[0052]** As can be seen from FIG. 6C, while the mask 110 is being tensed, the mask 110, the cover mask 130, and the frame 120 are joined together. As described above, the joining can be accomplished by any method, such as an adhesion or welding. However, laser dot welding is preferable, when considering an accuracy change or the like caused after the joining. When determining the welding pitch  $P_w$  between the welding dots 140, a change in the accuracy of the total pitch obtained after tension is removed, after the joining, must be considered. The relationship between a change in the total pitch and a change in the welding pitch when the tension has been removed after welding is shown in FIG. 8. As can be seen from FIG. 8, a variation in the total pitch decreases as the welding pitch decreases, and the variation in the total pitch is very small at the welding pitches of 3mm or less. Thus, it is preferable that the welding pitch  $P_w$  is 3mm or less. Under this condition, even when a mask is made of a Ni-Co alloy, welding dots are supported by a cover mask and a frame respectively installed on the upper and lower surfaces of the mask, such that a transformation of the mask due to heat refraction is prevented. Consequently, generation of cracks is prevented.

**[0053]** After the above-described welding is completed, a portion 142 of the cover mask 130 and the edge of the mask 110 may be cut off so that the sizes and shapes of the cover mask 130 and the mask 110 match with those of the frame 120.

**[0054]** This mask frame assembly may be used to vacuum-deposit an organic film or a second electrode layer for an organic EL device. Hereinafter, a method of manufacturing an organic EL device using the mask frame assembly will be described.

**[0055]** First, a substrate whose size corresponds to the size of the mask frame assembly 100 of FIG. 3 is prepared, and a first electrode layer is formed of ITO or the like in a predetermined pattern. Here, one first electrode layer pattern has the same size as the size of a mask unit 111 of the mask frame assembly 100 of FIG. 3, and the number of first electrode layer patterns is equal to the number of mask units 111. The first electrode layer may be formed by any of conventional pattern forming methods, but is usually formed by a photolithographic method.

**[0056]** After the first electrode layer patterns have been formed, an inter-insulator clearly partitioning the first electrode layer is formed of an insulating photosensitive material such as photoresist or polyimide. In some cases, a cathode separator partitioning a second electrode layer may be formed together with the inter-insulator.

**[0057]** Next, an organic film is deposited within a vacuum deposition device.

**[0058]** A depositing method depends on the type of an organic film to be deposited. Since a hole injection layer, a hole transport layer, an electron injection layer, or an electron transport layer is blanket-deposited without patterning, an open mask having no apertures is used instead of the deposition mask frame assembly of FIG. 3. An emission layer may be deposited using the deposition mask frame assembly of FIG. 3. These layers may be formed of any material that can form an organic film used in existing low-molecular organic EL devices, and are deposited in a sequence of the hole injection layer, the hole transport layer, the emissive layer, the electron transport layer, and the electron injection layer. Here, the structures of the deposited layers may be transformed into various structures.

**[0059]** After the completion of this organic film deposition, a second electrode layer serving as a cathode is deposited on the deposited organic film. The second electrode layer is patterned such that the second electrode layer patterns cross the first electrode layer patterns at approximately right angles, and may be formed of Al and/or Ca. The second electrode layer may be patterned by various methods, such as the above-described blanket deposition method using the open mask, or the deposition method using the deposition mask of FIG. 3.

**[0060]** After the deposition of the second electrode layer is completed, the second electrode layer is sealed with epoxy resin or a metal cap which contains a moisture absorbent, and a driving circuit is connected to a terminal exposed to the outside.

**[0061]** As described above, a mask frame assembly according to an embodiment of the present invention be used in the deposition of an organic film and the deposition of a second electrode layer.

**[0062]** The characteristics of an organic EL device manufactured using a mask frame assembly according to the present invention relative to an organic EL device using a conventional mask frame assembly are shown in Table 1. Table 1 shows different embodiments

where an emission layer is deposited using a mask frame assembly according to the present invention.

**[0063]** In Table 1, the first through third embodiments show organic EL devices manufactured using a mask frame assembly according to embodiments of the present invention, in which a cover mask is added to a mask formed of an Ni-Co alloy by electro-forming. The first comparative example shows an organic EL device using a mask formed of an Ni-Co alloy by a conventional electro-forming method. The second through fourth comparative examples show organic EL devices using a mask manufactured by etching.

	First embodiment	Second embodiment	Third embodiment	First comparative example	Second comparative example	Third comparative example	Fourth comparative example
$\Delta Pt$	$\pm 5\mu m$	$\pm 5\mu m$	$\pm 5\mu m$	$\pm 10\mu m$	$\pm 5\mu m$	$\pm 5\mu m$	$\pm 5\mu m$
$\Delta X$	$\pm 3\mu m$	$\pm 3\mu m$	$\pm 3\mu m$	$\pm 5\mu m$	$\pm 3\mu m$	$\pm 3\mu m$	$\pm 3\mu m$
$\Delta Ws1$	$\pm 5\mu m$	$\pm 5\mu m$	$\pm 5\mu m$	$\pm 5\mu m$	$\pm 10\mu m$	$\pm 10\mu m$	$\pm 10\mu m$
Pixel pitch	130ppi	150ppi	100ppi	130ppi	130ppi	100ppi	100ppi
Aperture efficiency	60%	55%	69%	60%	60%	69%	58%
Luminance failure rate	0%	0%	0%	9%	14%	12%	0%
Color mixture generation rate	0%	0%	0%	3%	5%	3%	0%
Blind generation rate	0%	0%	0%	0%	1.2%	1.2%	1.2%
Pixel short generation rate	0%	0%	0%	0%	0.5%	0.5%	0.5%

**[0064]** In Table 1,  $\Delta Pt$  denotes a deviation of a total pitch obtained after a tension has been removed after welding,  $\Delta X$  denotes a line deviation, and  $\Delta Ws1$  denotes a deviation of an

aperture width. The luminance failure rate is caused when an organic emission film is incompletely deposited on a pixel area of the organic EL device. The color mixture generation rate denotes a case in which two organic emission films are overlapped on a single pixel, that is, a case in which color mixture occurs. Accordingly, the luminance failure rate and the color mixture generation rate indicate when apertures formed in a mask have not been accurately patterned. The blind generation rate denotes a value obtained by dividing a blind that occurs at the same area on different substrates by the number of assessed pixels. The pixel short generation rate denotes a value obtained by dividing a pixel short that occurs at the same area on different substrates by the number of assessed pixels.

**[0065]** As can be seen from Table 1, the first through third embodiments according to the present invention provide a significantly lower luminance failure rate and a significantly lower color mixture generation rate than those of the second through fourth comparative examples in which a mask frame assembly manufactured by an existing etching method is used. Also, it can be seen from Table 1 that the present invention prevents generation of a blind or a pixel short.

**[0066]** Furthermore, the first through third embodiments of the present invention provide a lower luminance failure rate and a lower color mixture generation rate than those of the first comparative example in which a mask frame assembly manufactured by an existing electro-forming method is used. This is because in the first comparative example, a patterning failure occurs due to a degradation of the weldability of an Ni-Co alloy used to manufacture a mask of the mask frame assembly in the first comparative example.

**[0067]** FIG. 9 is a graph of an aperture efficiency versus a pixel pitch in cases I and II where a deviation ( $\Delta Ws1$ ) of the widths of apertures of a mask is  $\pm 5\mu\text{m}$  and  $\pm 10\mu\text{m}$ , respectively. The first through third embodiments of the present invention and the first comparative example in Table 1 correspond to the case I, and the second through fourth comparative examples in Table 1 correspond to the case II. As shown in FIG. 9, the present invention provides an aperture efficiency of 50% or greater even when pixels are made small enough to achieve a pixel pitch of 170ppi. Thus, the use of a deposition mask frame assembly according to the present invention enables a user to obtain a full-color organic EL device of a high quality.

**[0068]** Also, in a case in which a deposition mask is manufactured by electro-forming, shielding portions which define apertures may have a rectangular shape, thus reducing a shadow effect which occurs during deposition.

**[0069]** A deposition mask frame assembly according to the present invention, a method of manufacturing the same, and a method of manufacturing an organic EL device using the same provide the following effects. Firstly, generation of cracks due to welding of a mask and a frame is minimized, and transformation of the mask is also minimized.

**[0070]** Secondly, a welding failure can be minimized even when the mask is formed of an Ni-Co alloy, and the accuracy of the widths of apertures, the accuracy of a total pitch, and a surface smoothness can be increased simultaneously.

**[0071]** Thirdly, the deposition failure rate of pixels is lowered, such that generation of a luminance failure and a color mixture can be reduced.

**[0072]** Fourthly, pixels can be highly miniaturized with a high aperture efficiency, and an organic film or other electrodes can be deposited with a low loss. Thus, generation of a blind and a pixel short can be reduced.

**[0073]** Although a few embodiments of the present invention have been shown and described, it would be appreciated by those skilled in the art that changes may be made in these embodiments without departing from the principles and spirit of the invention, the scope of which is defined in the claims and their equivalents.